

White Paper

50V RF LDMOS

An ideal RF power technology for ISM, broadcast and commercial aerospace applications

freescale.com/RFpower

I. INTRODUCTION

RF laterally diffused MOS (LDMOS) is currently the dominant device technology used in high-power RF power amplifier (PA) applications for frequencies ranging from 1 MHz to greater than 3.5 GHz.

Beginning in the early 1990s, LDMOS has gained wide acceptance for cellular infrastructure PA applications, and now is the dominant RF power device technology for cellular infrastructure.

This device technology offered significant advantages over the previous incumbent device technology, the silicon bipolar transistor, providing superior linearity, efficiency, gain and lower cost packaging options.

LDMOS technology has continued to evolve to meet the ever more demanding requirements of the cellular infrastructure market, achieving higher levels of efficiency, gain, power and operational frequency^[1-8]. The LDMOS device structure is highly flexible. While the cellular infrastructure market has standardized on 28–32V operation, several years ago Freescale developed 50V processes for applications outside of cellular infrastructure. These 50V devices are targeted for use in a wide variety of applications where high power density is a key differentiator and include industrial, scientific, medical (ISM), broadcast and commercial aerospace applications.

Many of the same attributes that led to the displacement of bipolar transistors from the cellular infrastructure market in the early 1990s are equally valued in the broad RF power market: high power, gain, efficiency and linearity, low cost and outstanding reliability.

In addition, the RF power market demands the very high RF ruggedness that LDMOS can deliver. The enhanced ruggedness LDMOS devices available from Freescale can displace not only bipolar devices but VMOS and vacuum tube devices that are still used in some ISM, broadcast and commercial aerospace applications. The 50V devices designed by Freescale are fabricated on Freescale's unique very high voltage sixth-generation (VHV6) platform, and have been fully qualified and are shipping in volume. This paper describes the basic VHV6 device structure and the enhanced ruggedness variant (EVHV6), including advantages over competing device technologies. Ruggedness expectations and requirements for RF power devices targeting ISM applications are more stringent than for devices designed for less challenging applications like cellular infrastructure. This paper will include device and design considerations that specifically target enhancing ruggedness performance. The features of the products using this platform will also be presented.

II. LDMOS DEVICE TECHNOLOGY

Figure 1 depicts a cross section of a single finger of a typical LDMOS transistor. It includes a source metal region to electrically connect the N+ source to the P+ sinker, which in turn is connected to the back side source metal through the P+ substrate. This patented feature significantly lowers the source inductance to improve performance, but also allows the die to be directly attached onto an electrically and thermally conductive package flange to accommodate low-cost packaging platforms.

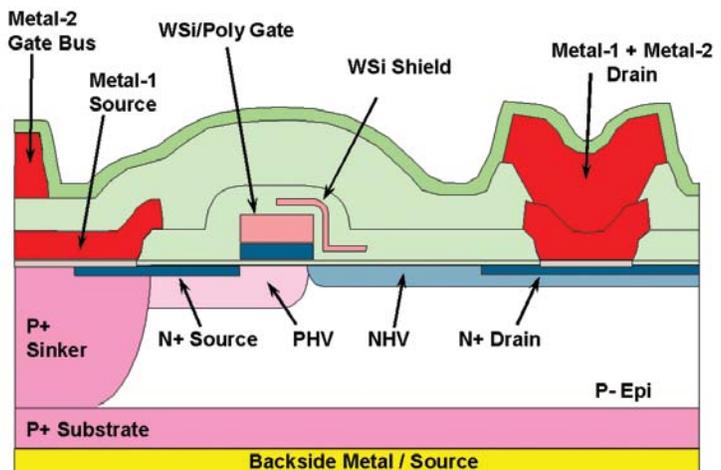


Figure 1: Cross section of an LDMOS device

The boron p-type “PHV” diffusion establishes the threshold voltage and turn-on characteristics of the device. The WSi/polysilicon gate provides a low gate access resistance, important for the large dimensions typical of RF power devices. A low doping concentration arsenic n-type “NHV” drift region between the gate and the highly doped N+ drain region is designed to support high breakdown voltages, low on-state resistance ($R_{DS(on)}$) and good hot carrier injection (HCI) reliability. The stacked aluminum drain metal is designed to meet electromigration specifications for high reliability. A metal-2 gate bus running parallel to the gate makes periodic connections to the gate WSi/polysilicon stack to reduce its resistance. Grounded shield structures (the ground strap is not shown in this figure) are also employed to reduce feedback capacitance between the drain and gate, and to control surface electric fields to allow for improved device performance without sacrificing breakdown voltage or HCI margin.

Another Freescale innovation pioneered in the cellular infrastructure market that is incorporated into the 50V LDMOS RF power product portfolio is an enhanced ESD protection structure that can tolerate moderate reverse bias conditions being applied to the gate lead (see Figure 2). An example of when this enhanced device is very beneficial is Class C operation at high input RF power levels. The RF swing could easily turn on a standard ESD structure during a small negative voltage swing, while the enhanced ESD device would remain off. The enhanced structure employed in the RF power products is much more robust against a broad range of operating conditions that may be encountered during operation.

A. Technology Comparison

The primary competitive technologies in the RF power market are the silicon vertical MOS (VMOS) device, and to a lesser extent 28V LDMOS. Compared to the LDMOS device, which is primarily a laterally fabricated device, the VMOS device has a significant vertical component to achieve the appropriate breakdown voltage. Vertical dimension and doping level control is inherently limited compared to surface or horizontal fabrication. Vertical structures typically

Attribute	Si VMOS	28V RF-LDMOS	50V RF-LDMOS
CW eff. at P1dB	3	5	5
Power Gain	3	5	5
Thermal resistance	3	4	5
CW Packaged Power Density	3	3	4
High Intrinsic Z_{in} / Z_{out} (wideband)	3	3	4
On-Die Passives Integration	2	4	4
Variability / Performance spread	2	4	4
Technology Maturity	5	5	4
Reliability	4	5	5

Table 1: Comparison of RF power attributes vs. device technology

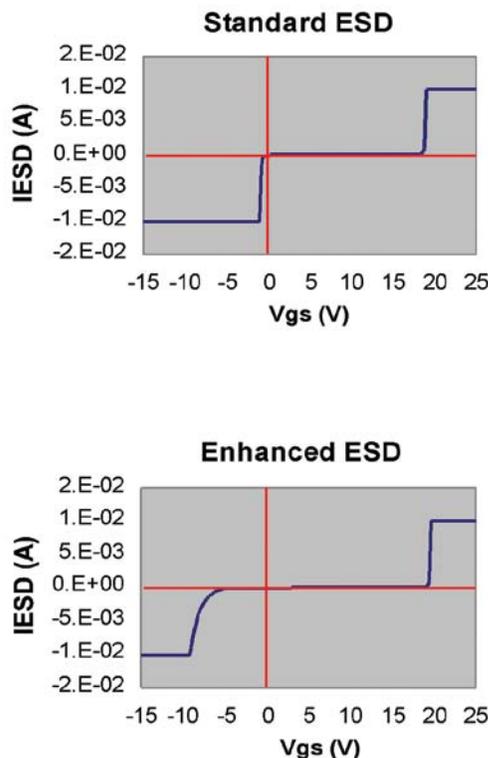


Figure 2: I-V characteristics of a standard and enhanced ESD protection device

rely on silicon epitaxy for both doping and thickness control, whereas lateral structures can leverage the deep sub- μm photolithography capability in modern fabs, while doping is determined with a high level of precision using ion implantation techniques (the same advanced techniques used in leading edge CMOS technologies).

A performance comparison of these three technologies (VMOS, 28V LDMOS and 50V LDMOS) is shown in Table 1 utilizing various metrics that are important for success in the RF power market. The color coding is red = poor, yellow = neutral, and green = strength.

The scale ranges from 1 to 5, with 5 being highest, or best. Starting down the metric list, LDMOS has superior gain and efficiency that can be traced to developments originally driven by the cellular infrastructure market where these parameters have long been of paramount importance, along with device structure advantages such as deep sub- μm self-aligned gates and shields to reduce feedback capacitance. The LDMOS devices have thermal resistance benefits as a result of having a backside source that can be connected directly to the thermally and electrically conductive package flange, which in turn is directly mounted to the heat sink. Typical VMOS devices have the drain on the backside of the wafer and require attaching the die to an electrically isolating flange material which increases the effective thermal resistance of this device structure. The excellent thermal conductivity of the LDMOS packaged products allows them to achieve significantly higher continuous wave (CW) power levels in a given package, especially the 50V technology with its inherently higher power density compared to the 28V variant. In addition, 50V LDMOS typically has 35% less output capacitance per watt (W) than competing 50V Si technologies, making it ideal for broadband applications.

LDMOS products in the cellular infrastructure market are typically manufactured with integrated matching networks, making the availability of on-die passives (inductors, capacitors) an LDMOS strength. The lateral nature of the LDMOS manufacturing flow leverages fab processes that can be controlled to very high precision levels, compared to VMOS that requires less well-controlled processes such as silicon epitaxy to form certain critical active regions of the structure, increasing variability and performance spread. Although VMOS and LDMOS are mature device technologies, the 50V LDMOS variant is a relative newcomer to the RF power market. Finally, LDMOS technology has a demonstrated track record of providing outstanding reliability with nearly 20 years of widespread deployment in the demanding cellular infrastructure market.

B. Technology Development Trends

Freescale has a unique advantage in having robust development programs for both 28V and 50V LDMOS, and in being a leading supplier to both the cellular infrastructure market and the ISM, broadcast and commercial aerospace markets. This cross-fertilization of development programs accelerates development in all these areas, and extends the impact of R&D investments across a broader product space.

Several trends have emerged over the past few years. Figure 3 highlights four that are applicable to both cellular infrastructure as well as the other RF power markets. The first is increased frequency of operation, with products already qualified for operation up to 3.8 GHz for 28V; Freescale's 50V platform supports products with frequencies exceeding 3 GHz. The second trend is the release of high power, multi-stage ICs, or discrete devices with integrated input and output matching networks. These high-power RF devices are common in the cellular infrastructure market. Products are in development for other RF power markets that include integrated matching networks to simplify ease of use while maintaining broadband performance.

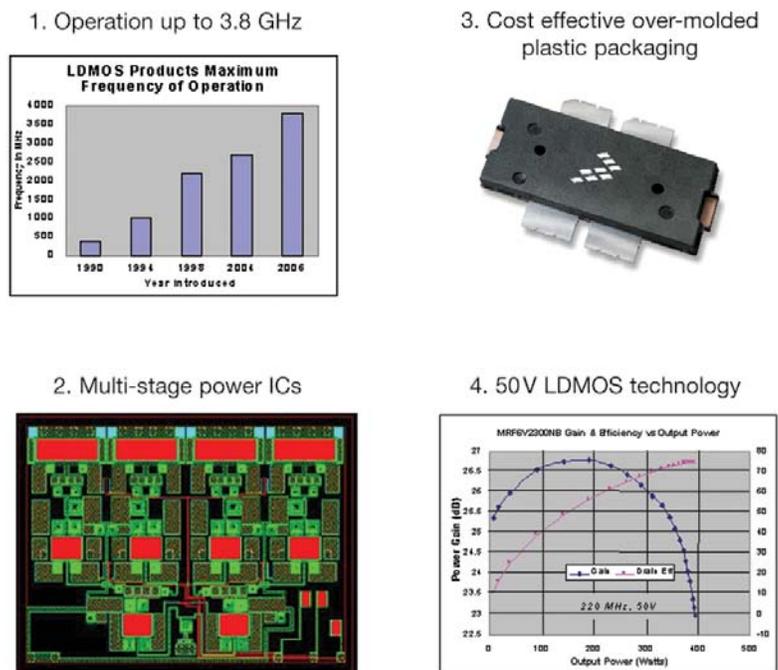


Figure 3: LDMOS development trends

The third major trend is the adoption of over-molded plastic (OMP) for high-power RF applications. OMP is the lowest cost packaging technology available; Freescale has a leadership position pioneering OMP for cellular infrastructure applications, and has leveraged this experience into the RF power product portfolio. Package development within Freescale continues, with the primary emphasis on increasing the power level that can be accommodated. The final trend is to continue to invest heavily in 50V LDMOS development for the RF power market.

III. RUGGEDNESS ENHANCEMENT

A. Ruggedness in MOSFETs

Ruggedness failure in MOSFETs is a catastrophic failure of the device due to internal power dissipation. It does not occur as a result of normal operation of the device within a power amplifier designed according to established RF design and mechanical engineering principles. The ruggedness failure of a MOSFET is the result of a drain breakdown (impact ionization) event. The ionization event occurs due to the distribution of charges internally within the MOSFET which are driven by the intrinsic gate and drain terminal waveforms. Figures 4a and 4b show a generic common source PA circuit using a MOSFET and a more detailed schematic diagram of a MOSFET, showing the parasitic elements.

There are three basic ruggedness failure mechanisms that can occur as a result of a drain impact ionization event. Any one of these mechanisms can result in extremely high power dissipation within the MOSFET and cause thermal damage—these mechanisms are illustrated by the schematic in Figure 4b. The first two mechanisms involve the basic breakdown of the MOSFET drain junction—either laterally across the channel or vertically across the drain to source junction isolation. The third mechanism is triggered by an impact ionization event and is the self biasing and “snapback” of the parasitic bipolar device—a drain ionization event being a necessary pre-condition to this behavior. If sufficient internal MOSFET power dissipation occurs from one of these ionization events, and exceeds the normal thermal limitations of the device, catastrophic device failure can result. The bipolar snapback behavior is particularly problematic as there is a positive feedback mechanism with temperature which can result in the well-documented thermal runaway phenomena for bipolar junction transistors (BJTs).

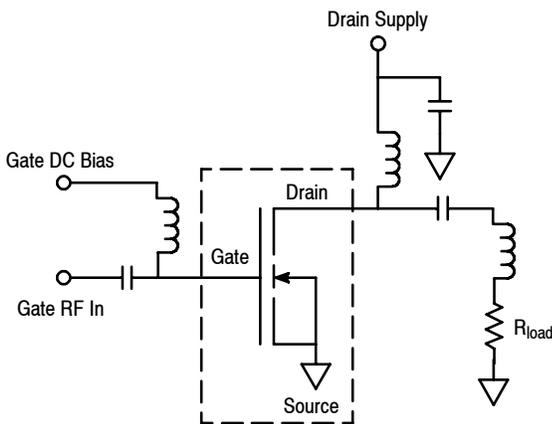


Figure 4a: Common source PA

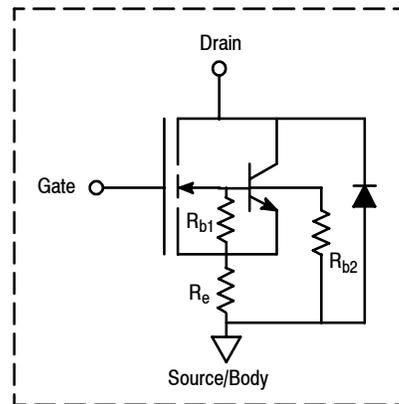


Figure 4b: MOSFET schematic showing parasitic elements

B. LDMOS Ruggedness Improvement

The ruggedness behavior of a MOSFET cannot be separated from the matching networks of the PA or the source and loads provided to the PA. Fundamental device improvements can, however, be incorporated into the MOSFET to improve the ability of the device to withstand the stresses applied by the PA. Internal device structure changes can be made to address the three impact ionization mechanisms to alter the conditions under which the ionization events occur and to change the parasitic bipolar device characteristics. Figure 5 illustrates a cross section of a VHV6 LDMOS device from source to drain and shows impact ionization rates and locations for three different designs.

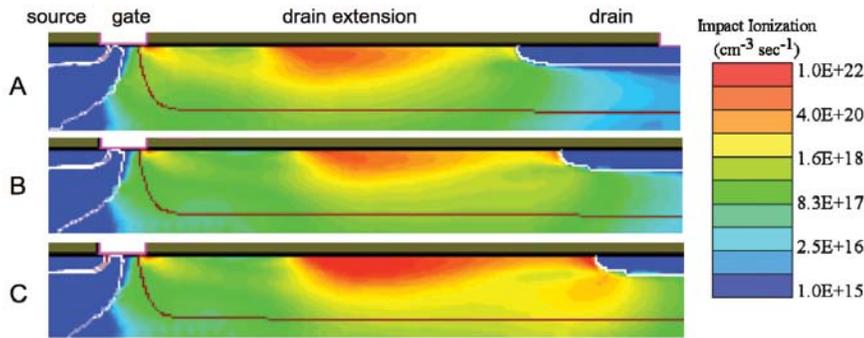


Figure 5: Impact ionization for VHV6 LDMOS device designs

Practical ruggedness characterization for RF PAs like LDMOS generally involve altering the operating characteristics of the PA (load mismatch, larger drain supply voltage, shorter signal rise time) to increase the stress on the MOSFET to determine the point of failure.

Freescall uses two main methods to test the ruggedness of our devices:

- 1) Operation into high levels of impedance mismatch: measured by the corresponding level of load voltage standing wave ratio (VSWR)
- 2) Unclamped inductive switch test where the energy absorption from a test inductor is measured

The second method uses an Integrated Technologies Corporation Unclamped Inductive Load Tester, model #ITC55100B, to measure the maximum energy dissipation capability of the device under these high-current and highVage test conditions.

Figure 6 shows the internal diagram of the ITC55100B tester.

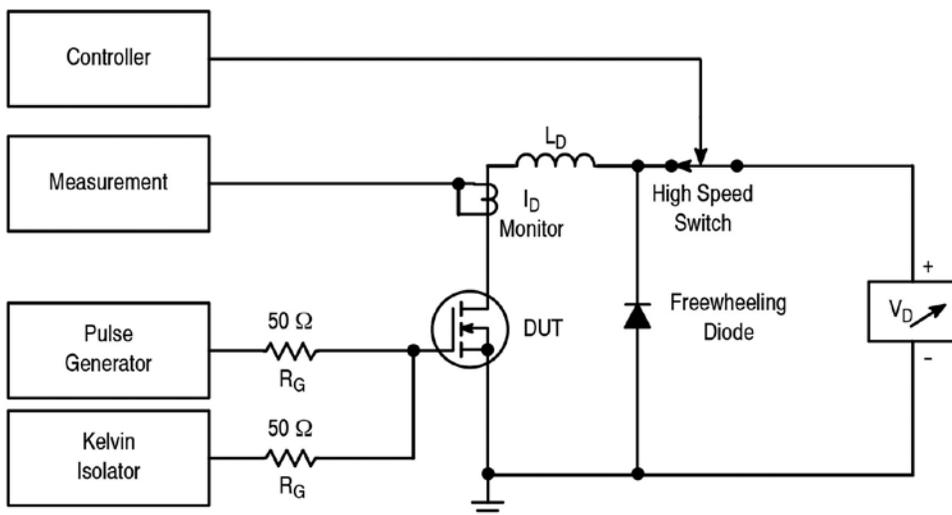
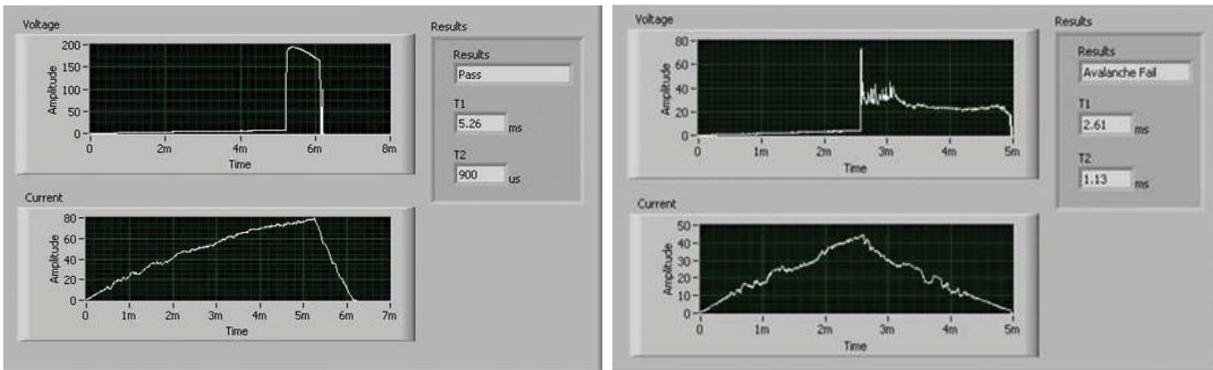


Figure 6: Internal diagram of the ITC55100B tester

The tester controller activates the pulse generator to turn on the device under test (DUT) through the limiting and terminating resistor, R_G , creating a very clean gate pulse waveform. This pulse waveform tests the maximum energy dissipation capability of the DUT by stressing it under various controlled energy levels. This is accomplished by attaching an unclamped inductive load to the device's drain and source connection and then increasing both the load current and load voltage up until the point that the DUT failure is achieved. This test method for power devices gives repeatable, quantitative and reliable data needed to evaluate an LDMOS transistor's ability to survive stresses that could cause an avalanche mode failure. The final maximum energy dissipation capability rating, in joules, is calculated by the following equation:

$$E = \frac{1}{2} \times L \times I^2 \quad \text{where } L \text{ is the load inductance value and } I \text{ is the peak current within the load inductor.}$$

Figure 7 shows how internal device engineering has had a major positive influence on the ruggedness of the devices in these tests.



1.25 kW device absorbs 5.30 joules and survives

Non-rugged 1 kW devices fail after absorbing 1.53 joules

Figure 7: Voltage and current curves during energy discharge

Parameter	1 kW Non-Rugged	1 kW Rugged	Improvement Factor
Max Voltage	164V	195V	+18%
$I_{D\ peak}$	40A	80A	+100%
Energy Absorbed	1.53J	5.30J	+240%

Table 2: Impact of ruggedness design changes

Freescale developed the EVHV6 50V LDMOS process for industrial applications such as plasma generators, CO_2 lasers and MRIs, where withstanding extremely high VSWRs is a requirement. This EVHV6 process enhancement to the VHV6 technology creates devices that can withstand VSWRs greater than 65:1 at all phase angles at their rated power.

Freescale has developed a process where improved ruggedness does not compromise RF performance, making Freescale E series devices suitable for any application where ruggedness would be a benefit.

IV. DESIGN FEATURES

This section will cover the design features for the 50V RF power devices. RF performance, thermal characteristics, device impedances and device models will be included.

A. 50V Ruggedized Devices

Freescale now offers four new ultra-rugged 50V power devices designed for ISM applications. These 50V devices cover power levels from 300W to 1.25 kW and frequencies from 1.8 MHz to 860 MHz. Subscribe to Freescale's *Design News* newsletter to receive information on new product releases.⁽⁹⁾

Product	Power Level	Frequency Range	Package Style	Package Type
MRFE6VP61K25H	1250W	1.8–600 MHz	Push-Pull	Air Cavity Ceramic
MRFE6VP5600H	600W	1.8–600 MHz	Push-Pull	Air Cavity Ceramic
MRFE6VP8600H	600W 125W Avg. (DVB-T)	470–860 MHz	Push-Pull	Air Cavity Ceramic
MRFE6VP6300H	300W	1.8–600 MHz	Push-Pull	Air Cavity Ceramic

Table 3: Freescale ruggedized 50V product offerings

B. 50V ISM and Commercial Aerospace Power Devices

Freescale offers many different 50V power devices targeting the ISM band. These 50V devices are available at different power levels and package styles. Table 4 shows the 50V LDMOS product offerings currently available from Freescale. Power levels range from 10W to 1000W, covering frequencies from 1.8 MHz to 1400 MHz.

Product	Power Level	Frequency Range	Package Style	Package Type
MRF6VP41KH	1000W	10–500 MHz	Push-Pull	Air Cavity Ceramic
MRF6VP11KH	1000W	1.8–150 MHz	Push-Pull	Air Cavity Ceramic
MRF6VP2600H	600W	1.8–500 MHz	Push-Pull	Air Cavity Ceramic
MRF6VP3450H	450W	470–860 MHz	Push-Pull	Air Cavity Ceramic
MRFE6VP6300H	300W	1.8–600 MHz	Push-Pull	Air Cavity Ceramic
MRF6V4300N	300W	10–600 MHz	Single-Ended	Over-Molded Plastic
MRF6V2300N	300W	10–600 MHz	Single-Ended	Over-Molded Plastic
MRF6V2150N	150W	10–450 MHz	Single-Ended	Over-Molded Plastic
MRF6V3090N	90W	470–860 MHz	Single-Ended	Over-Molded Plastic
MRF6VP3091N	90W	470–860 MHz	Push-Pull	Over-Molded Plastic
MRF6V2010N	10W	10–450 MHz	Single-Ended	Over-Molded Plastic
MRF6VP121KH	1 kW Pulsed	965–1215 MHz	Push-Pull	Air Cavity Ceramic
MRF6V12500H	500W Pulsed	960–1215 MHz	Single-Ended	Air Cavity Ceramic
MRF6V14300H	300W Pulsed	1200–1400 MHz	Single-Ended	Air Cavity Ceramic
MRF6V13250H	250W	1300 MHz	Single-Ended	Air Cavity Ceramic
MRF6V12250H	250W Pulsed	960–1215 MHz	Single-Ended	Air Cavity Ceramic
MRF6V10010N	10W Pulsed	960–1400 MHz	Single-Ended	Over-Molded Plastic

Table 4: Freescale standard 50V product offerings

C. Examples of 50V Power Devices

The MRFE6VP61K25H is a versatile device and is well suited for a wide range of applications. It is capable of delivering over 1 kW CW and will withstand extreme mismatches, even at rated output power. This is due to its high efficiency, low thermal resistance and ruggedized silicon design.

An excellent example of an application of this device can be seen in the reference circuit for the 87.5–108 MHz FM broadcast band. Over this frequency range, the device has output power greater than 1100W, gain greater than 24 dB and drain efficiency greater than 80%. Performance was characterized using the 87.5–108 MHz application circuit as shown in Figure 8.

Figure 9 shows the broadband performance for the 87.5–108 MHz application circuit.

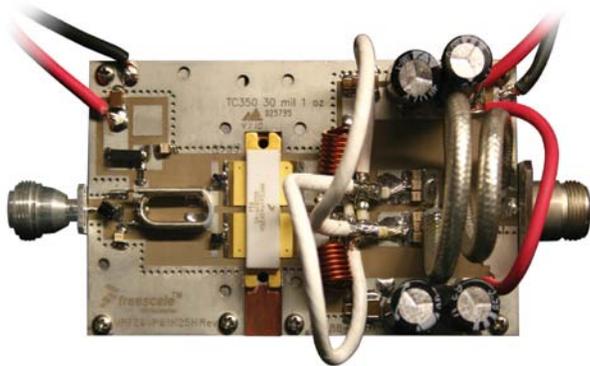


Figure 8: 87.5–108 MHz FM broadcast application circuit

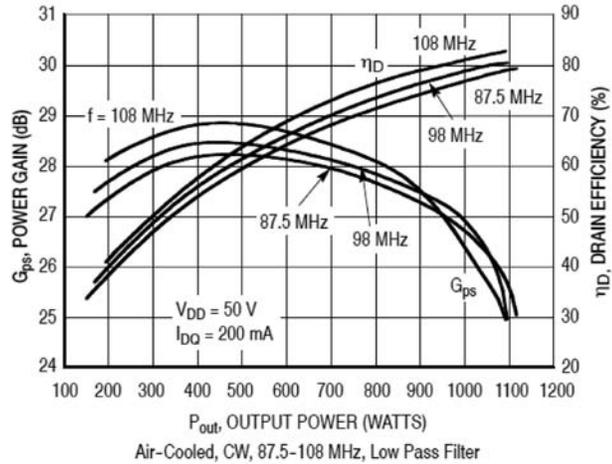


Figure 9: CW performance graph with low pass filter versus output power

As another example, the MRF6V12500HS has been designed to cover the 960 to 1215 MHz frequency range. Figure 10 shows the compact broadband circuit board layout of only 3.2 x 2.2 inches.

Typical performance for this 960 to 1215 MHz pulsed design is shown in Figure 11. In this test circuit with 500W output, the gain is more than 17.5 dB with better than 1 dB gain flatness and drain efficiency is greater than 56%.

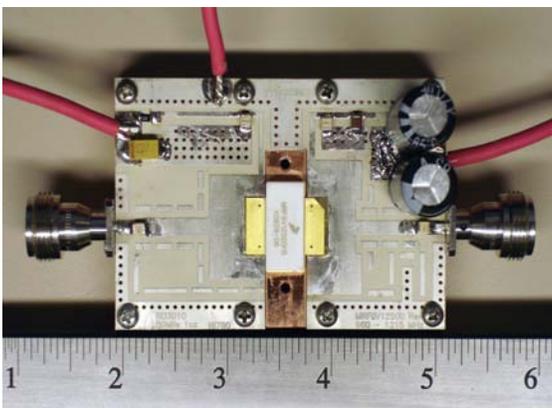


Figure 10: MRF6V12500HS broadband fixture

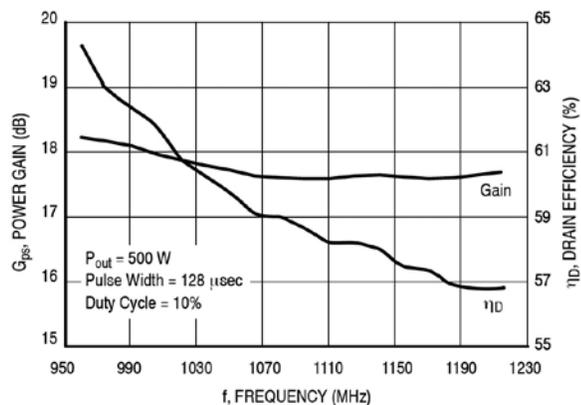


Figure 11: MRF6V12500HS RF performance curves circuit performance

D. 50V LDMOS Thermal Performance

Freescale 50V LDMOS devices have been designed for both excellent RF and thermal performance in intended applications. The devices are optimized thermally for both pulse and CW applications.

Figure 12 shows a plot of transient thermal impedance for the MRFE6VP61K25H device under various pulse conditions. The bottom axis shows pulse width in seconds and curves for two different duty cycles. As an example, a pulse width of 100 μ sec and a duty cycle of 10% shows a θ_{jc} of 0.22°C/W. From this graph the CW θ_{jc} can be seen to be 0.15°C/W.

Figure 13 shows the MTTF versus junction temperature for CW conditions. This graph assumes a power output of 1250W CW, a drain voltage of 50 Vdc and a drain efficiency over 74%. As an example, the graph shows that at a 150°C junction temperature, the MTTF is approximately 4.5 million hours, or 513 years.

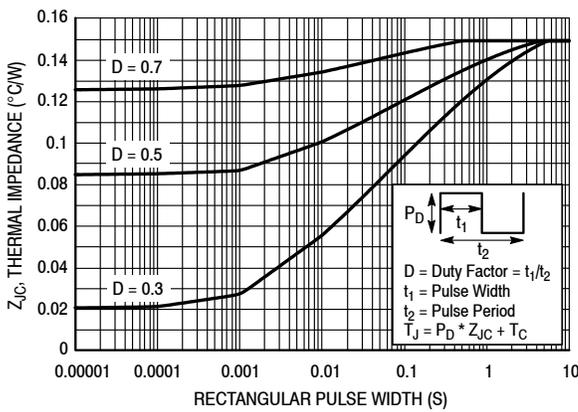


Figure 12: MRFE6VP61K25H transient thermal impedance

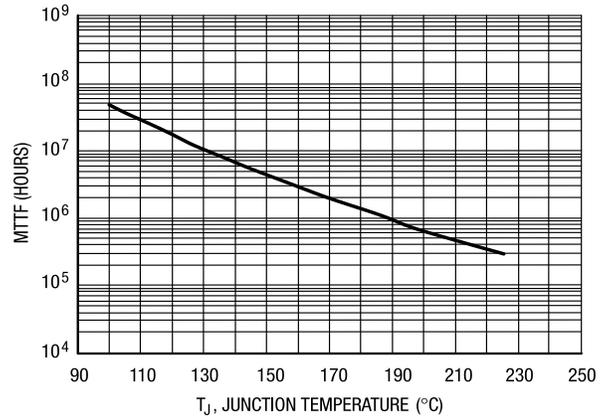
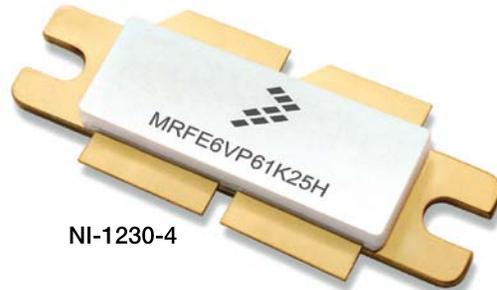


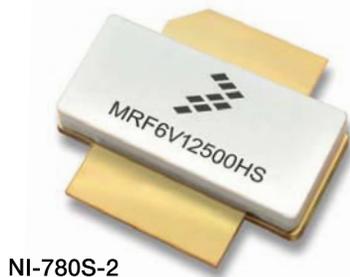
Figure 13: MTTF versus junction temperature for MRFE6VP61K25H



TO-270 WB-4



NI-1230-4



NI-780S-2



NI-780S-4

E. 50V LDMOS Device Models

Models are available to assist customers simulating designs using Freescale 50V LDMOS devices. Table 5 shows the status of models for currently available devices.

Product	Agilent ADS	AWR Microwave Office®	Product	Agilent ADS	AWR Microwave Office
MRFE6VP61K25H	Now	Now	MRF6VP41KH	Now	Now
MRFE6VP5600H	Now	Now	MRF6V14300H	Now	Now
MRFE6VP6300H	Now	Now	MRF6V13250H	Now	Now
MRFE6VP8600H	9/2011	9/2011	MRF6V10010N	Now	-
MRF6V2010N	Now	Now	MRF6V12250H	Now	Now
MRF6V2150N	Now	Now	MRF6V3090N	Now	Now
MRF6V2300N	Now	Now	MRF6VP3091N	9/2011	9/2011
MRF6V4300N	Now	Now	MRF6VP121KH	-	-
MRF6VP2600H	Now	Now	MRF6VP3450H	Now	Now
MRF6VP11KH	Now	Now	MRF6V12500H	Now	Now

Table 5: Freescale 50V product models

As an example of the benefits of using Freescale 50V LDMOS product models, Figure 14 shows the RF performance curves for the MRF6V3090N with both measured data in a broadband test fixture and product model simulations for a 960 to 1215 MHz L-band pulsed application. Table 6 shows a comparison of the measured versus simulated performance results under pulsed conditions.

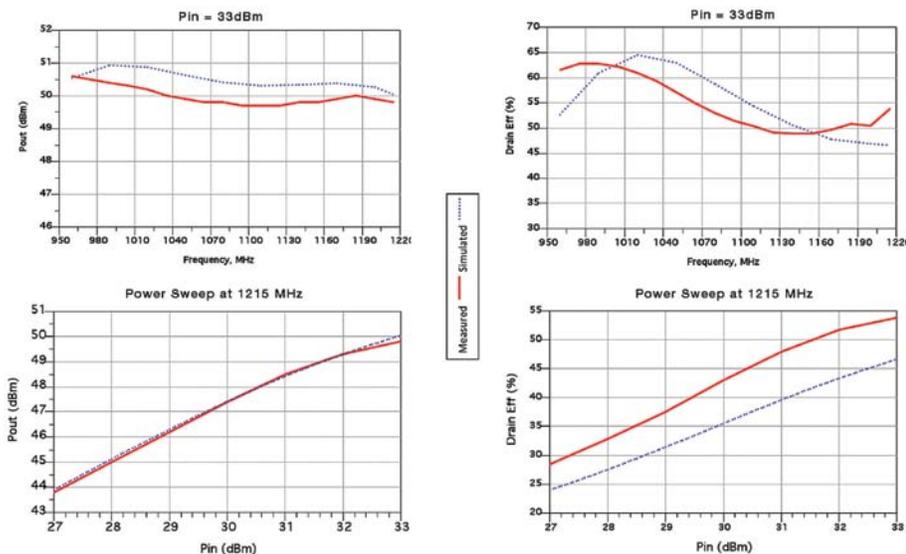


Figure 14: MRF6V3090N RF performance curves, simulated versus measured
Pulse width = 128 μ sec, duty cycle = 10%

Frequency	Power Level	Simulated		Measured	
		Power Gain	Drain Efficiency	Power Gain	Drain Efficiency
960 MHz	90W	17.7 dB	47.7%	18.2 dB	55.1%
1090 MHz	90W	18.1 dB	54.3%	17.3 dB	51.2%
1215 MHz	90W	17.2 dB	44.4%	17.2 dB	51.7%

Table 6: MRF6V3090N RF performance, simulated versus measured
Pulse width = 128 μ sec, duty cycle = 10%

V. SUMMARY

Freescale has successfully leveraged its position as the world's leading supplier of high-power RF LDMOS transistors to develop, qualify and release to manufacturing a portfolio of 50V LDMOS products specifically designed for the unique requirements of the ISM, broadcast and commercial aerospace market segments. Compared to the existing competitors and technologies used in these market segments, Freescale's 50V LDMOS provides superior power, gain, linearity, efficiency and ruggedness.

This paper has described the device technology along with key features, presented details on how extreme ruggedness is achieved and outlined performance and design features of the portfolio. Freescale is committed to delivering compelling solutions to the RF power market, including an aggressive development program to maintain Freescale's innovative leadership.

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